Guidelines for EDTM Paper with 14-pt Title even for 2 Rows

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ABSTRACT

This abstract is a brief (75 words) synopsis of your **3-page camera-ready** paper.

Keywords: Manufacturing, CMOS and SOI

INTRODUCTION

This template has been tailored for output on A4- or letter-sized paper. Margins, column widths, line spacing, and type styles are built-in; examples of the type styles are provided throughout this document and are identified in italic type, within parentheses, following the example, for the Electron Devices Technology and Manufacturing conference (EDTM) [1]. Final camera ready 3-page paper of text with 2 columns, figures and tables should be submitted by October 31, 2024. The paper should explain why and how it was done, principal results, and their significances.

FORMATS AND FONTS

14, 12 and 10 pt of Times New Roman are used for the title, author/affiliation and text, respectively. In particular, the use of the International System of Units (SI Units) is advocated. And use a zero before decimal points: "0.25", not ".25".

A. Equations

10-pt Italic of Times New Roman is used for the equation, as shown in Eq. 1. The number of equation within parentheses are to position flush right.

$$y = f(x) \tag{1}$$

B. References

When referring to them in the text, type the corresponding reference number in square brackets as shown at the end of this sentence [1].

C. Table

8 pt of Times New Roman is used for the caption, as shown in Table 1.

D. Figure

Note that the digest of EDTM will be provided as electronic information. The font size in the figures should be large enough to make it readable in the printed version on A4 paper. 8 pt of Times New Roman is also used for the caption.

CONCLUSION

Summarize the contents of paper. And finally, don't forget to check the spelling.

REFERENCES

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TABLE I: List of Font sizes

Text	Type	Font
Title	Bold	14
Authors		12
Affiliation		12
Headings	Bold	10
Sub-headingds	Italic	10
Main text		10
Equations	Italic	10
References		8
Footnotes		8
Table caption		8

Fig. 1. Logos of the IEEE, EDS and EDTM.